

This diagram shows a cross-sectional view of a semiconductor device. A central channel 102 is formed between two gate stacks 105. The gate stacks 105 are composed of a top layer 106a and a bottom layer 106b. The device includes multiple layers 101, 103, 104, 106, 107, and 108. The layers 101, 103, and 104 are located on the right side of the device, while the layers 106, 107, and 108 are located on the left side. The layers 101 and 103 are separated by a layer 104. The layers 106 and 107 are separated by a layer 108. The layers 101 and 103 are also separated by a layer 104. The layers 106 and 107 are separated by a layer 108. The layers 101 and 103 are also separated by a layer 104. The layers 106 and 107 are separated by a layer 108.